

PWR-INT301

High-side Driver IC

Floating Inputs

Floating High-side Drive



Product Highlights

Floating Control Inputs

- Connects directly to PWR-INT300 HSD outputs
- No external level translators or transformers required

Gate Drive Output for an External MOSFET or IGBT

- Provides 1 A sink/500 mA source current
- Can drive MOSFET or IGBT gate at up to 20 V
- Floating source for driving high-side N-channel MOSFET or IGBT
- External MOSFET or IGBT allows flexibility in design

Built-in Protection Circuits

- Logic inputs include noise immunity circuitry
- Undervoltage lockout

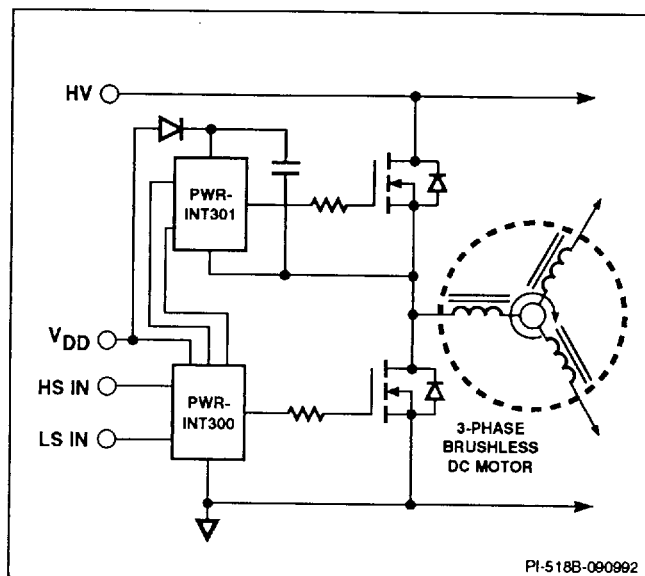


Figure 1. Typical Application.

Description

The PWR-INT301 high-side driver IC provides gate drive for an external high-side MOSFET or IGBT switch. When used in conjunction with the PWR-INT300 low-side drivers, the PWR-INT301 provides a simple, cost-effective interface between low-voltage control logic and high-voltage MOSFET or IGBT switches.

Built-in circuitry shared between the PWR-INT301 and the PWR-INT300 provides noise immunity. The PWR-INT301 is powered from a ground-referenced low-voltage supply. It derives a floating supply from this rail by using a simple bootstrap technique to provide adequate gate drive for the external MOSFET or IGBT.

Applications include motor drives and half and full bridge power supplies.

The PWR-INT301 is available in an 8-pin plastic DIP package.

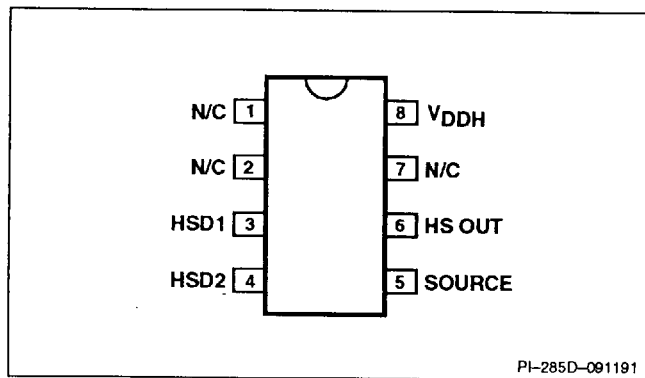
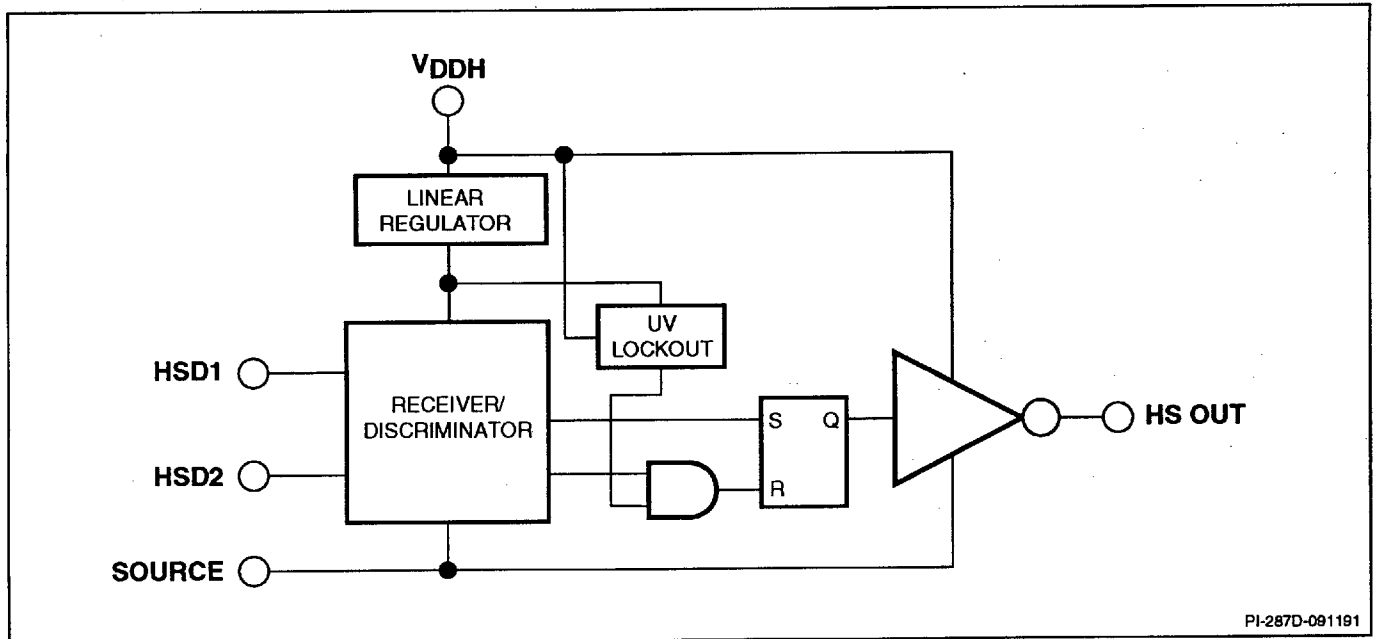


Figure 2. Pin Configuration.

ORDERING INFORMATION		
PART NUMBER	PACKAGE	TEMP RANGE
PWR-INT301PFI	8-pin PDIP	-40 to 85°C



PI-287D-091191

Figure 3. Functional Block Diagram of the PWR-INT301.

PWR-INT301 Functional Description

5 V Regulator

The 5 V linear regulator circuit provides the supply voltage for the receiver/discriminator circuit and control logic. This allows the logic section and the driver circuitry to utilize separate supply voltages without the need of two external supplies.

Undervoltage Lockout

The undervoltage lockout circuit disables the HS OUT pin until the V_{DDH} power supply has exceeded 9.25 V (typical), guaranteeing that the high side MOSFET or IGBT will be off during power-up.

Receiver/Discriminator Circuit

This circuit provides noise immunity by rejecting common-mode noise on the HSD inputs.

Driver

The CMOS driver circuit provides drive power to the gate of the MOSFET or IGBT. The driver consists of a CMOS buffer capable of driving external transistors at up to 20 V. The SOURCE pin is connected to the source of the external MOSFET or IGBT to establish a reference for the gate voltage.



Pin Functional Description

Pin 1, 2:
No connection.

Pin 3:
Level shift input **HSD1** works in conjunction with **HSD2** to provide interface from the low side control logic and to give noise immunity.

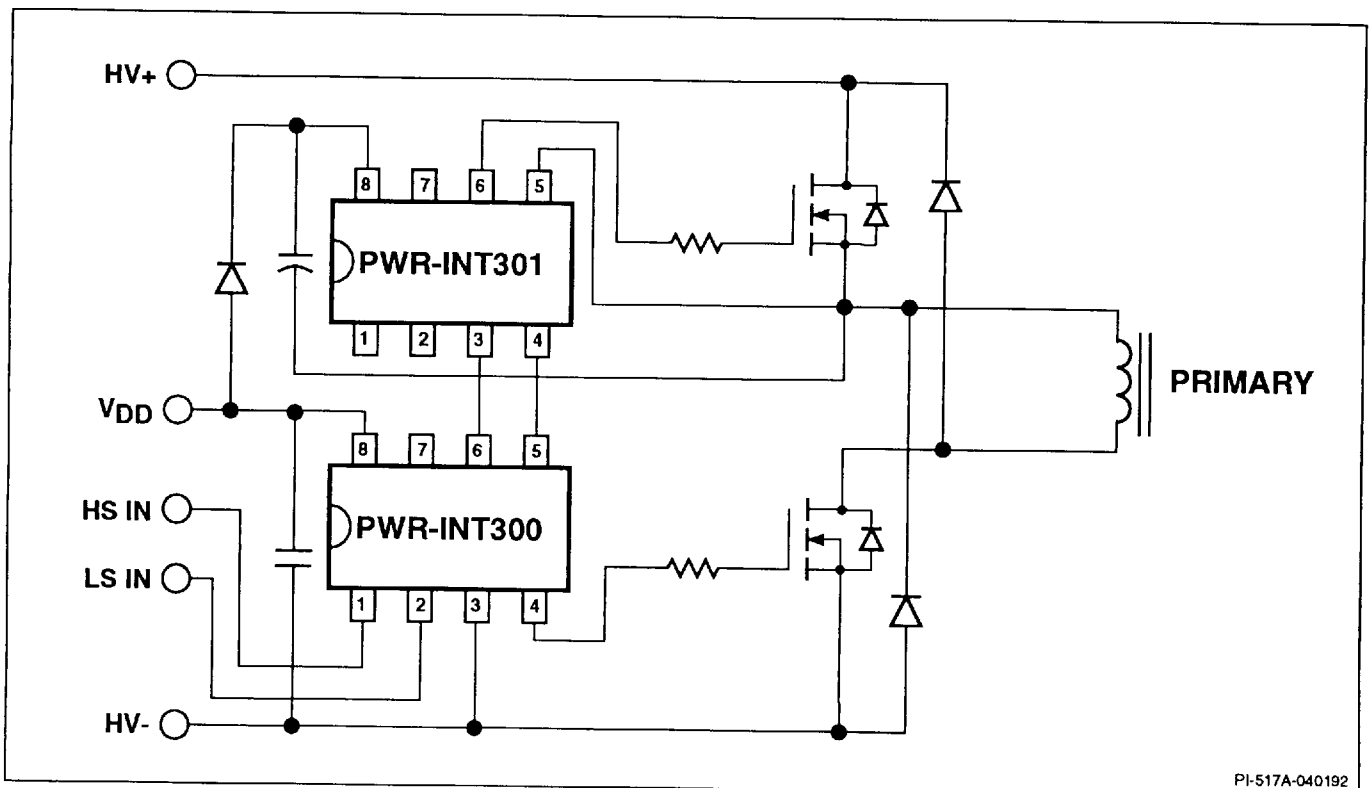
Pin 4:
Level shift input **HSD2** works in conjunction with **HSD1** to provide interface from the low side control logic and to give noise immunity.

Pin 5:
SOURCE connection. Analog reference point for the circuit, normally connected to the source of the high side MOSFET or IGBT.

Pin 6:
HS OUT is the output of the MOSFET or IGBT driver for the high side.

Pin 7:
No connection.

Pin 8:
 V_{DDH} supplies power to the control logic and output driver.



PI-517A-040192

Figure 4. The PWR-INT300 and PWR-INT301 Driving a Two Transistor Forward Converter.

ABSOLUTE MAXIMUM RATINGS¹

V_{DD} Voltage	22 V	Lead Temperature ⁽²⁾	260°C
Storage Temperature	-65 to 165°C	Power Dissipation	1.0 W
Ambient Temperature	-40 to 85°C	Thermal Impedance (θ_{JA})	100°C/W
Junction Temperature	150°C		

1. Unless noted, all voltages referenced to COM, $T_A = 25^\circ\text{C}$
2. 1/16" from case for 5 seconds.

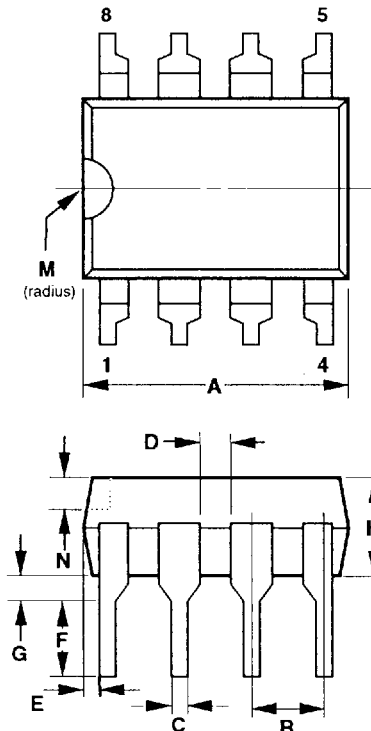


Specification	Symbol	Test Conditions, Unless Otherwise Specified: $V_{DD} = 20\text{ V}$, $COM = 0\text{ V}$ $T_A = -40\text{ to }85^\circ\text{C}$	Limits			Units
			MIN	TYP	MAX	
HSD INPUTS						
Input Current Threshold	I_{IN}			2.5	5	mA
HS OUT						
Output Voltage, High	V_{OH}	$I_o = -65\text{ mA}$	$V_{DD}-1.0$			V
Output Voltage, Low	V_{OL}	$I_o = 130\text{ mA}$			1.0	V
Output Short Circuit Current	I_{OS}	$V_o = 0\text{ V}$	-0.5			A
		$V_o = V_{DD}$	1			
Propagation Delay	t_{PLH}, t_{PHL}	$C_L = 1000\text{ pF}$			200	ns
Rise Time	t_r	$C_L = 1000\text{ pF}$		50		ns
Fall Time	t_f	$C_L = 1000\text{ pF}$		25		ns
SYSTEM RESPONSE						
Matching (Low On to High On)	Mt_{P+}	High t_{PLH} - Low t_{PLH}			50	ns
Matching (Low Off to High Off)	Mt_{P-}	High t_{PHL} - Low t_{PHL}			50	ns
UNDERVOLTAGE LOCKOUT						
Undervoltage Threshold	V_{UV}		8.5	9.25	10	V
Undervoltage Hysteresis	V_{UH}		0.75		1.55	V

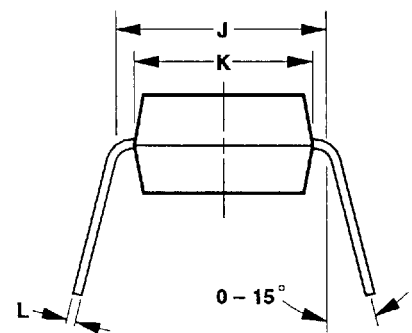


Specification	Symbol	Test Conditions, Unless Otherwise Specified: $V_{DD} = 20\text{ V}$, $COM = 0\text{ V}$ $T_A = -40\text{ to }85^\circ\text{ C}$	Limits			Units
			MIN	TYP	MAX	
SUPPLY						
Supply Current	I_{DD}			1.1	2.0	mA
Supply Voltage	V_{DD}		10		20	V

DIM	Inches	mm
A	.395 MAX	10.033 MAX
B	.090-.110	2.286-2.794
C	.015-.021	.381-.533
D	.040 TYP	1.016 TYP
E	.010-.040	.254-1.016
F	.125 MIN	3.175 MIN
G	.020 MIN	.508 MIN
H	.125-.135	3.175-3.429
J	.300-.320	7.620-8.128
K	.245-.255	6.223-6.477
L	.009-.015	.229-.381
M	.030-.110	.762-2.794
N	.020 TYP	.508 TYP



**8-Pin Plastic DIP
PF Suffix**



PO-001-071289

